## NSN 5961-01-020-1610

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View Online at https://aerobasegroup.com/nsn/5961-01-020-1610 **Inclosure Material:** Glass **Overall Length:** 0.260 inches **Overall Height:** 0.080 inches Overall Width: 0.150 inches **Component Name And Quantity:** 2 transistor **Mounting Method: Terminal Semiconductor Material:** Silicon all transistor Voltage Rating In Volts Per Characteristic: 60.0 collector to base voltage/static/emitter open all transistor and 40.0 collector to emitter voltage/static/base open all transistor and 5.0 emitter to base voltage, static, collector open all transistor **Current Rating Per Characteristic:** 500.00 amperes source cutoff current all transistor **Power Rating Per Characteristic:** 350.0 milliwatts small-signal input power, common-collector absolute all transistor **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** All transistor junction pattern arrangement: npn **Test Data Document:** 27963-57651000 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Terminal Type And Quantity:** 6 pin Shelf Life: N/a **Unit Of Measure: Demilitarization:** No